General Description

The WSR88P06 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

Product Summery

BVDSS	RDSON	ID
-60V	9.0mΩ	-88A

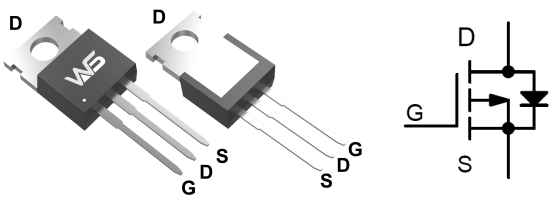
Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

Features

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

TO-220 Pin Configuration



Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-60	V
VGS	Gate-Source Voltage	±20	V
ID@TC=25℃	Continuous Drain Current, -VGS @ -10V1	-88	A
ID@TC=100℃	Continuous Drain Current, -VGS @ -10V1	-50	A
IDM	Pulsed Drain Current2	-320	A
EAS	Single Pulse Avalanche Energy3	450	mJ
IAS	Avalanche Current	41	A
PD@TC=25℃	Total Power Dissipation4	110	W
TSTG	Storage Temperature Range	-55 to 150	℃
TJ	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Rating	Units
RθJA	Thermal Resistance Junction-Ambient 1	1.1	℃/W
RθJC	Thermal Resistance Junction-Case1	60	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-60	-68	---	V
△BVDSS/△TJ	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.035	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance2	V_{GS}=-10V , I_D=-20A	---	9.0	11	mΩ
		V_{GS}=-4.5V , I_D=-15A	---	12	16	
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	-1.8	-2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.28	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-60V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-60V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-20A	---	50	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.0	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-30V , V_{GS}=-10V , I_D=-20A	---	56	---	nC
Q_{gs}	Gate-Source Charge		---	11	---	
Q_{gd}	Gate-Drain Charge		---	9	---	
Td(on)	Turn-On Delay Time	V_{DD}=-30V , V_{GS}=-10V , R_G=3Ω, I_D=-20A	---	4.5	---	ns
T_r	Rise Time		---	2.5	---	
Td(off)	Turn-Off Delay Time		---	14.5	---	
T_f	Fall Time		---	3.8	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	3500	---	pF
C_{oss}	Output Capacitance		---	600	---	
C_{rss}	Reverse Transfer Capacitance		---	25	---	
I_S	Continuous Source Current1,5	V_G=V_D=0V , Force Current	---	---	-80	A
I_{SM}	Pulsed Source Current2,5		---	---	-240	A
V_{SD}	Diode Forward Voltage2	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The EAS data shows Max. rating . The test condition is VDD =-48V,VGS =-10V,L=0.1mH,IAS =-41A

4、The power dissipation is limited by 150℃ junction temperature

5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Typical Characteristics

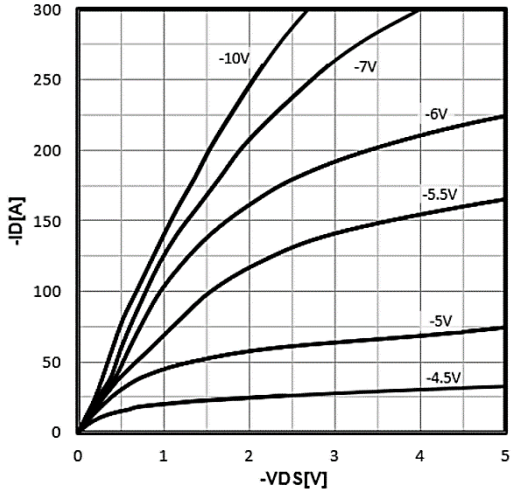


Figure 1. Type. Output Characteristics (Tj=25 ℃)

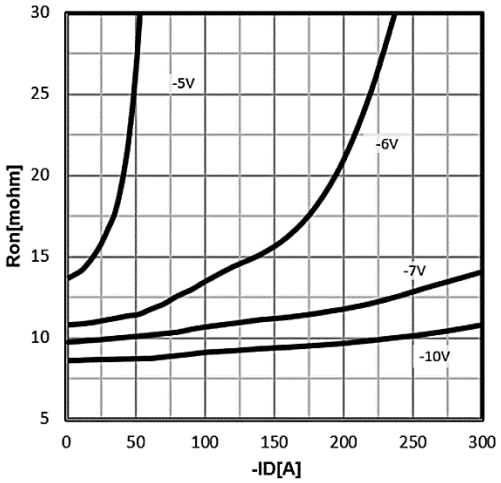


Figure 2. Type. drain-source on resistance

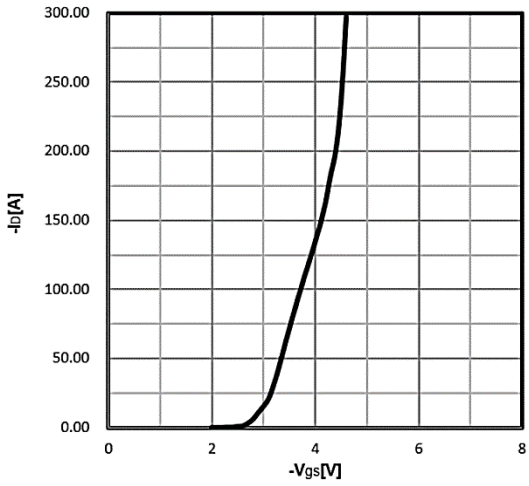


Figure 3. Type. transfer characteristics

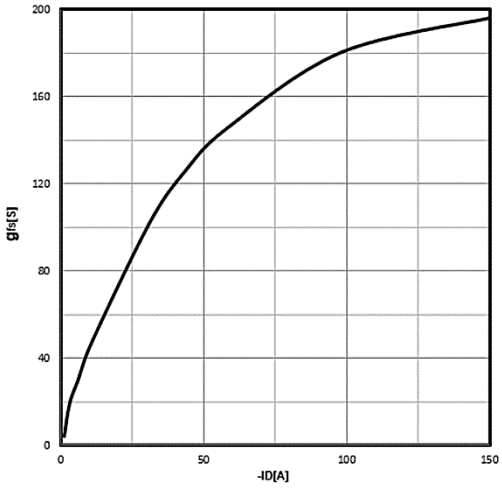


Figure 4. Type. forward transconductance

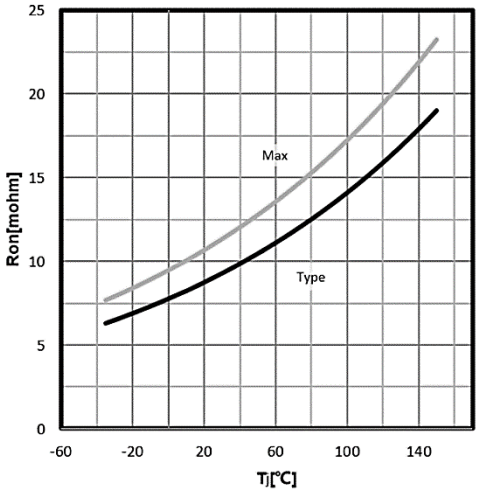


Figure 5. Drain-source on-state resistance
RDS(on) =f(Tj); ID =80A; VGS =10V

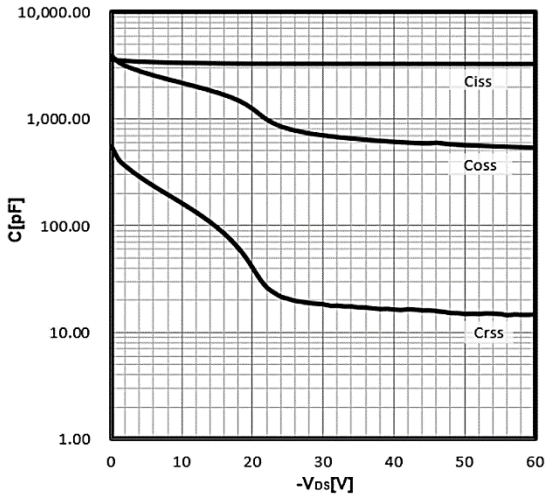


Figure 6 . Body-Diode Characteristics
C=f(VDS); VGS =0V; f=1MHz

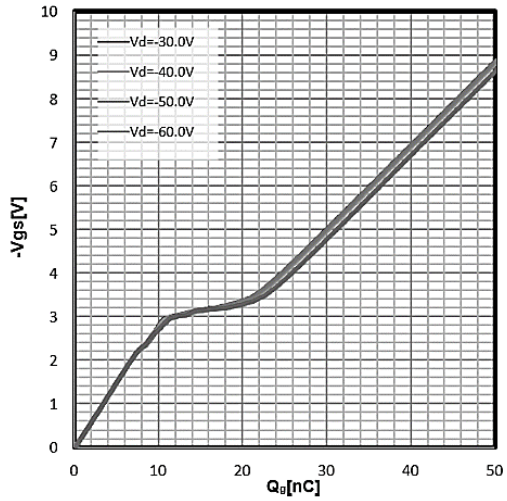


Figure 7. Typ. gate charge
VGS =f(Q gate) ; ID =20A

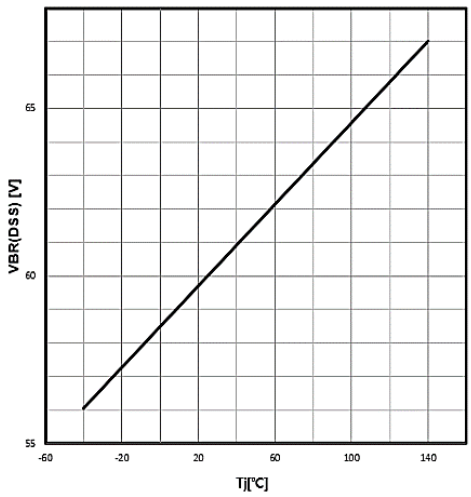


Figure 8. Drain Current Derating
VBR(DSS) =f(T j); I D =250uA

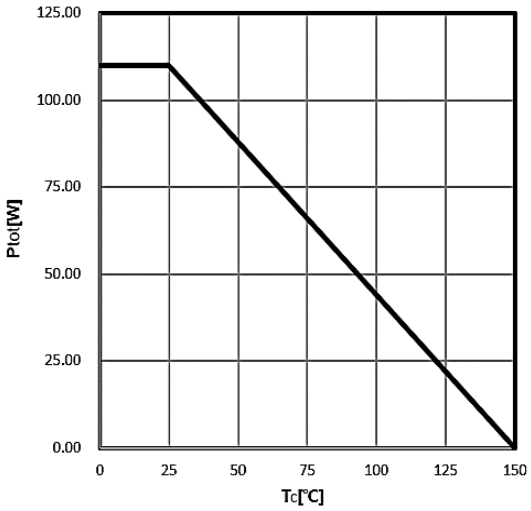


Figure 7. Power Dissipation

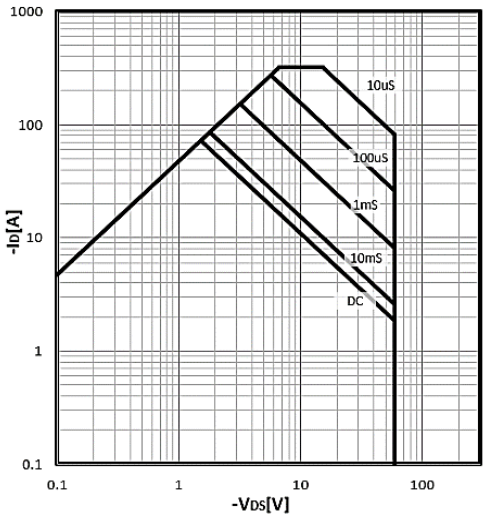


Figure 8. Safe operating area

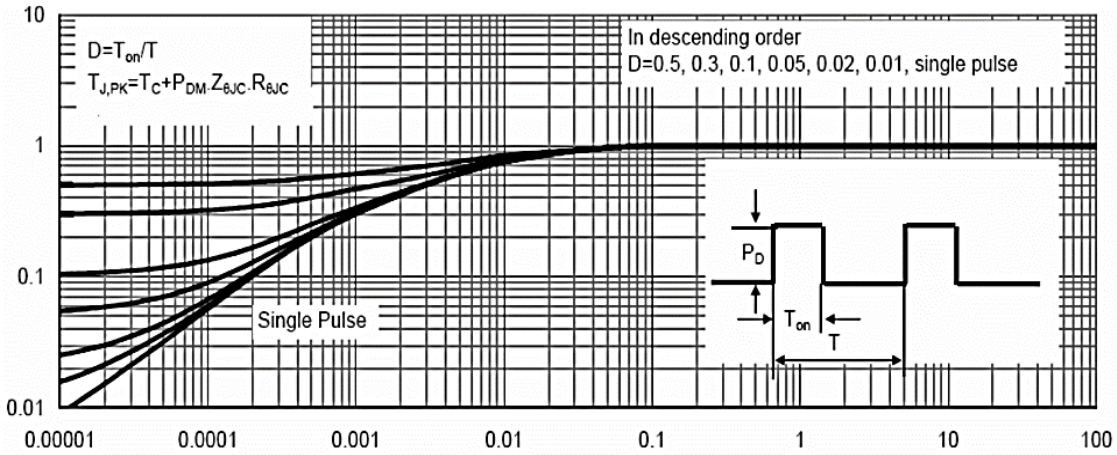


Figure 10. Max. transient thermal impedance

ZthJC =f(tp)

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